	Application No.	Applicant(s)	
Notice of Allowability	10/721,659	KOH, KWAN-JU	
	Examiner	Art Unit)
	Theresa T Doan	2814	مهم
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap or other appropriate communicatio GHTS. This application is subject t	plication. If not include n will be mailed in due	ed course. THIS
1. $igspace$ This communication is responsive to <u>Election/Restriction fil</u>	led 10/22/04.		
2. The allowed claim(s) is/are 3-10.		•	
3. The drawings filed on are accepted by the Examine.	г.		
 4. Acknowledgment is made of a claim for foreign priority ur a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 	been received. been received in Application No cuments have been received in this of this communication to file a reply	national stage applica	
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give			IOTICE OF
6. CORRECTED DRAWINGS (as "replacement sheets") mus (a) ☐ including changes required by the Notice of Draftspers 1) ☐ hereto or 2) ☐ to Paper No./Mail Date (b) ☒ including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t 7. ☐ DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT	son's Patent Drawing Review (PTO). s Amendment / Comment or in the (1.84(c)) should be written on the drawing he header according to 37 CFR 1.121 sit of BIOLOGICAL MATERIAL	Office action of ngs in the front (not the (d).	
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/O Paper No./Mail Date 03/18/04 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	5. ☐ Notice of Informal I 6. ☐ Interview Summary Paper No./Mail Da 7. ☑ Examiner's Amend 8. ☑ Examiner's Statem 9. ☐ Other	r (PTO-413), ite ment/Comment	,

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DETAILED ACTION

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

IN THE DRAWINGS:

Figure 1 is labeled as --PRIOR ART-- (See MPEP 608.02 (g)).

Reasons for Allowance

- 2. Claims 3-10 are allowed.
- 3. The following is an examiner's statement of reasons for allowance:

The prior art of record fails to disclose the combination of a method of fabricating a semiconductor device recited in the base claim 3. Specifically, the combination of the process comprising forming a first mask film and a second mask film on the first interlayer insulation film sequentially; forming a first etch mask to be used to form air gaps by selectively etching the second mask film; depositing a third mask film on the first etch mask and the first mask film; forming a second etch mask by etching the third mask film and exposed the first mask film, wherein the second etch mask is made from

the third mask film remaining on side walls of the first etch mask and the first mask film remaining below the first etch mask and the third mask film; removing the first etch mask and simultaneously forming open pores in the first interlayer insulation film by etching the first etch mask and exposed the first interlayer insulator film using the second etch mask; forming air gaps comprising closed pores in the first interlayer film at an interlevel between upper metal wire layers and the lower metal wire layers by forming a second interlayer insulation film after removing the second etch mask.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Theresa T Doan whose telephone number is (571) 272-1704. The examiner can normally be reached on Monday to Thursday from 8:00AM -6:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, WAEL FAHMY can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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December 8, 2004.

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